



Technical Data Sheet

ACS Material Mechanically Exfoliated Single Crystal Graphene On SiO₂/Si (SiO₂: 90nm Thick)

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Revision: 062317

1. Preparation Method

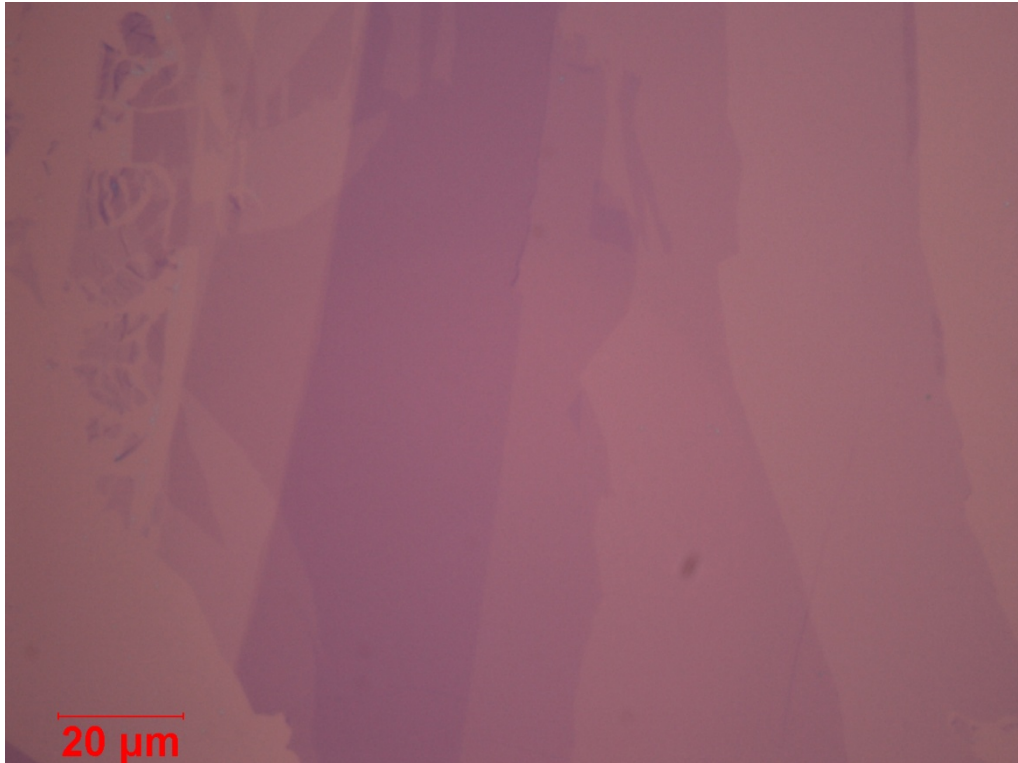
Mechanical Exfoliation method

2. Characterizations

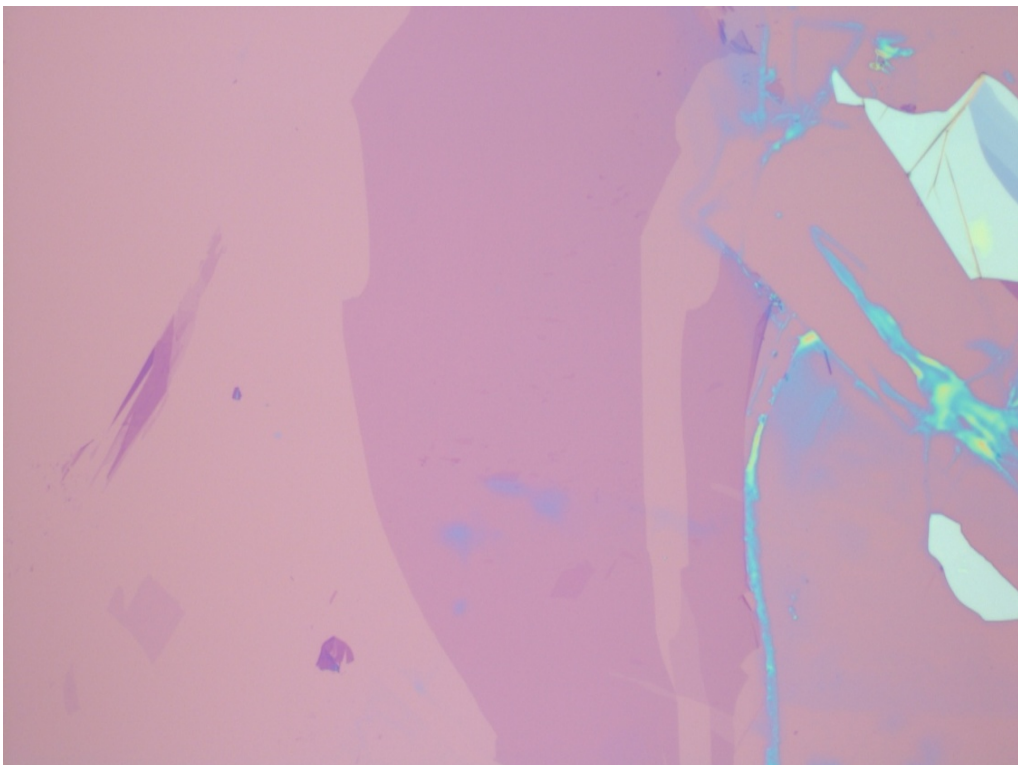
Graphene Layer	Monolayer, Single Crystal	Bilayer, Single Crystal
Substrate:	SiO ₂ / Si	SiO ₂ / Si
Substrate size:	1cm x 1cm 1.5cm x 1.5cm 2cm x 2cm	1cm x 1cm 1.5cm x 1.5cm 2cm x 2cm
Thickness of SiO ₂ :	90 nm	90 nm
Thickness of Si:	500 μm	500 μm
Graphene Area:	>5000 μm ²	>5000 μm ²



Typical Image of ACS Material Mechanically Exfoliated Monolayer Graphene on 90nm SiO₂



Typical Image of ACS Material Mechanically Exfoliated Monolayer Graphene on 90nm SiO₂



Typical Image of ACS Material Mechanically Exfoliated Bilayer Graphene on 90nm SiO₂

3. Application Fields

- 1) Gas-sensitive materials
- 2) Electronic displays
- 3) Composite materials

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